



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

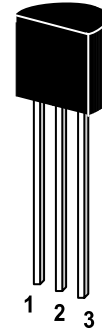
TEL: 852-2790 0314 FAX: 852-2790 0206

ST 2N3704

NPN Silicon Epitaxial Planar Transistor

for general purpose applications.

On special request, these transistors can be
manufactured in different pin configurations.

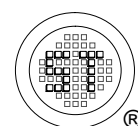


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_c	600	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$



Dated : 02/04/2005



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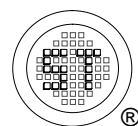
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Characteristics at $T_{amb}=25^{\circ}C$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=2V, I_C=50mA$	$*h_{FE}$	100	-	300	-
Collector Base Breakdown Voltage at $I_C=100\mu A$	BV_{CBO}	50	-	-	V
Collector Emitter Breakdown Voltage at $I_C=10mA$	$*BV_{CEO}$	30	-	-	V
Emitter Base Breakdown Voltage at $I_E=100\mu A$	BV_{EBO}	5	-	-	V
Collector Cutoff Current at $V_{CB}=20V$	I_{CBO}	-	-	100	nA
Emitter Cutoff Current at $V_{BE}=3V$	I_{EBO}	-	-	100	nA
Output Capacitance at $V_{CB}=10V, f=1MHz$	Cob	-	-	12	pF
Collector Emitter Saturation Voltage at $I_C=100mA, I_B=5mA$	$*V_{CE(sat)}$	-	-	0.6	V
Base Emitter On Voltage at $V_{CE}=2V, I_C=100mA$	$*V_{BE(on)}$	0.5	-	1	V
Current Gain Bandwidth Product at $V_{CE}=2V, I_C=50mA, f=20MHz$	f_T	100	-	-	MHz

* Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.



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